STB100NH02L

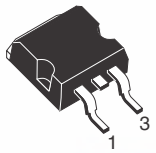
N-channel 24V - 0.0052Ω - 60A - D²PAK STripFET™ III Power MOSFET

General features

Type	V_{DSS}	$R_{DS(on)}$	I_D
STB100NH02L	24V	<0.006Ω	60A(1)

1. Value limited by wire bonding

- $R_{DS(ON)}$ * Q_g industry's benchmark
- Conduction losses reduced
- Switching losses reduced
- Low threshold device

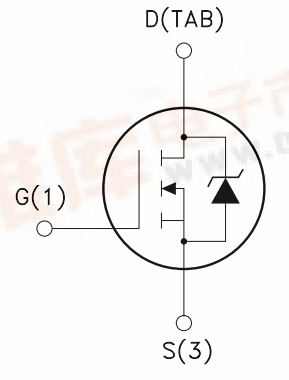


D²PAK

Description

The STB100NH02L utilizes the latest advanced design rules of ST's proprietary STripFET™ technology. This is suitable fot the most demanding DC-DC converter applications where high efficiency is to be achieved.

Internal schematic diagram



Applications

- Switching application

Order codes

Part number	Marking	Package	Packaging
STB100NH02LT4	B100NH02L	D²PAK	Tape & reel

Contents

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{spike} (1)	Drain-source voltage rating	30	V
V_{DS}	Drain-source voltage (V_{GS} = 0)	24	V
V_{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	24	V
V_{GS}	Gate- source voltage	± 20	V
I_D (2)	Drain current (continuous) at T_C = 25°C	60	A
I_D (2)	Drain current (continuous) at T_C = 100°C	60	A
I_{DM} (3)	Drain current (pulsed)	240	A
P_{tot}	Total dissipation at T_C = 25°C	100	W
	Derating Factor	0.67	W/°C
E_{AS} (4)	Single pulse avalanche energy	600	mJ
T_{stg}	Storage temperature	-55 to 175	°C
T_j	Max. operating junction temperature		

1. Garanted when external Rg=4.7Ω and t_f < tfmax.
2. Value limited by wire bonding
3. Pulse width limited by safe operating area.
4. Starting T_j = 25 °C, I_D = 30A, V_{DD} = 15V

Table 2. Thermal data

Rthj-case	Thermal resistance junction-case max	1.5	°C/W
Rthj-amb	Thermal resistance junction-ambient max	62.5	°C/W
T_J	Maximum lead temperature for soldering purpose	300	°C

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 25mA, V_{GS} =0	24			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0) V_{DS} = 20V V_{DS} = 20V, T_C = 125°C				1 10	µA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 20V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250µA	1	1.8		V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10V, I_D = 30A V_{GS} = 5V, I_D = 15A		0.0052 0.007	0.006 0.011	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 10V , I_D = 30A		40		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 15V, f = 1MHz, V_{GS} = 0		2850 800 120		pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 10V, I_D = 30A R_G = 4.7Ω V_{GS} = 10V (see *Figure 13*)		13 75 50 18		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 10V, I_D = 30A, V_{GS} = 10V, R_G = 4.7Ω (see *Figure 14*)		47.5 10 7	64	nC nC nC
R_G	Gate input resistance	f=1 MHz gate DC Bias=0 test signal level =20 mV open drain		1		Ω

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.

Table 5. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)				60 240	A A
V_{SD} (2)	Forward on voltage	I_{SD} = 30A, V_{GS} = 0			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 60A, di/dt = 100A/µs, V_{DD} = 16V, T_j = 150°C (see *Figure 15*)		35 35 2		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

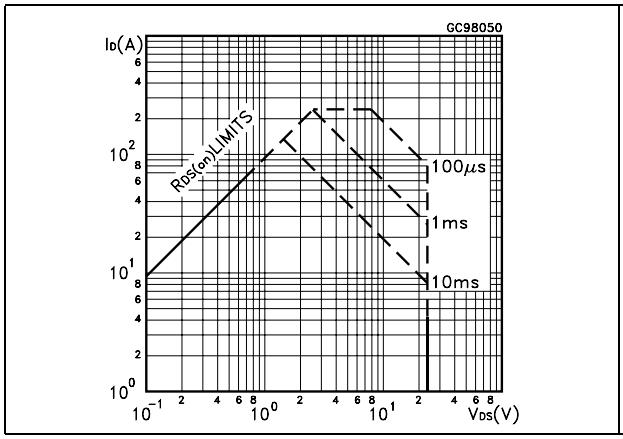


Figure 2. Thermal impedance

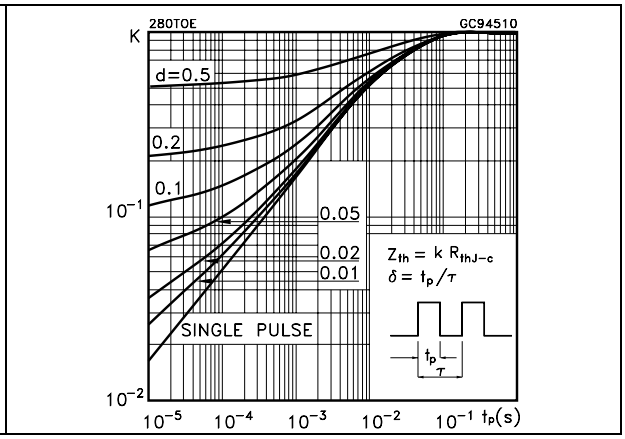


Figure 3. Output characterisics

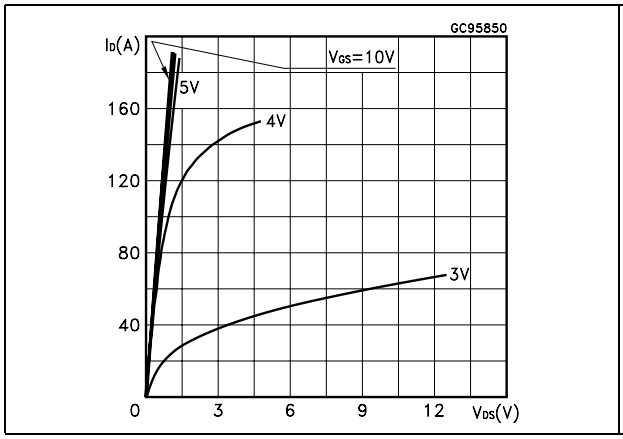


Figure 4. Transfer characteristics

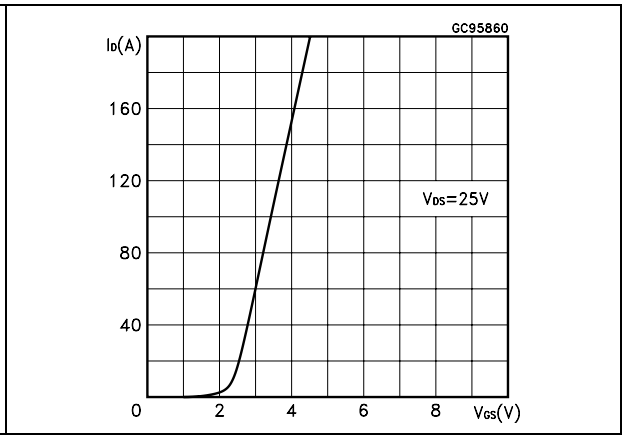


Figure 5. Transconductance

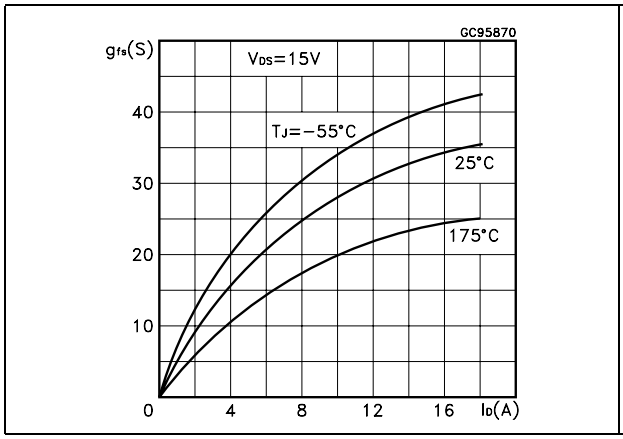


Figure 6. Static drain-source on resistance

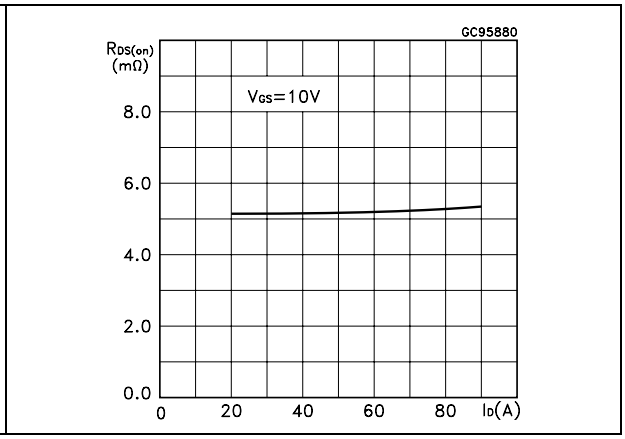


Figure 7. Gate charge vs gate-source voltage

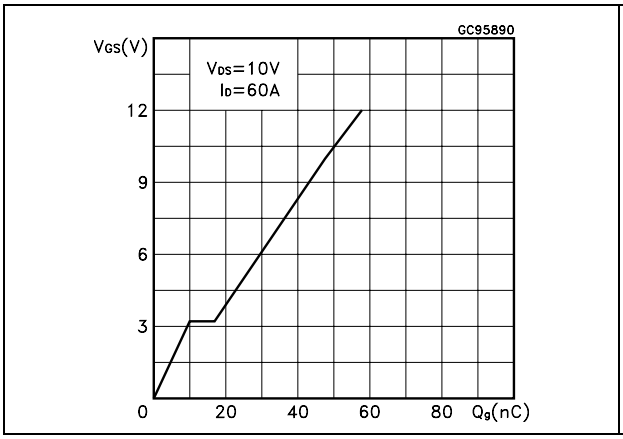


Figure 8. Capacitance variations

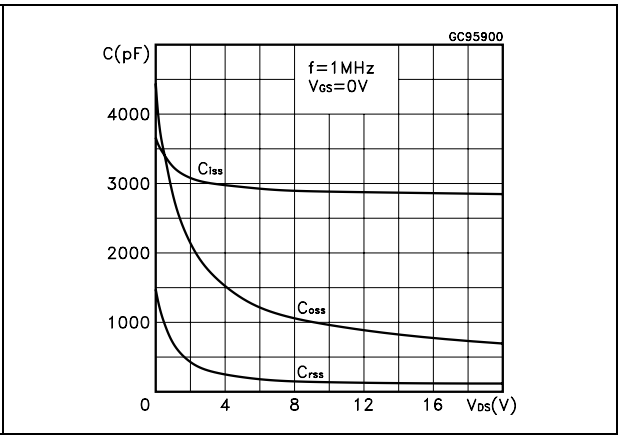


Figure 9. Normalized gate threshold voltage vs temperature

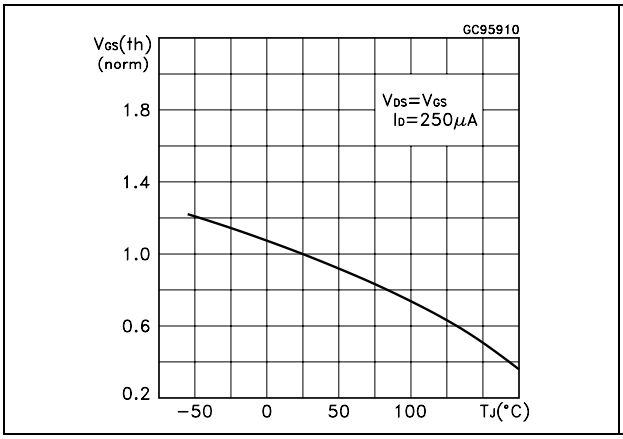


Figure 10. Normalized on resistance vs temperature

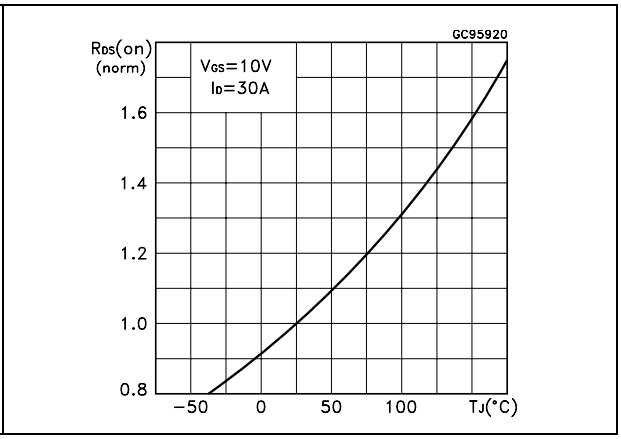


Figure 11. Source-drain diode forward characteristics

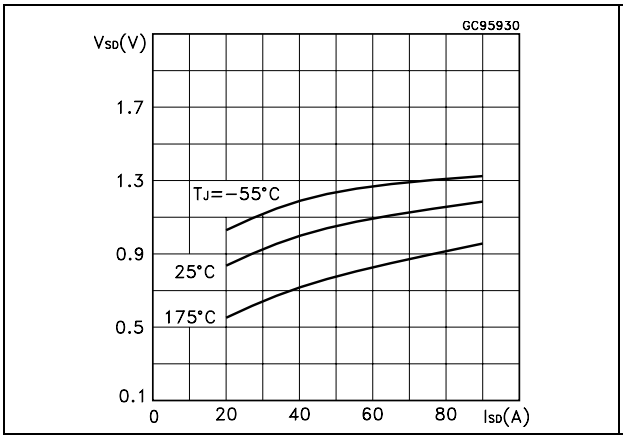
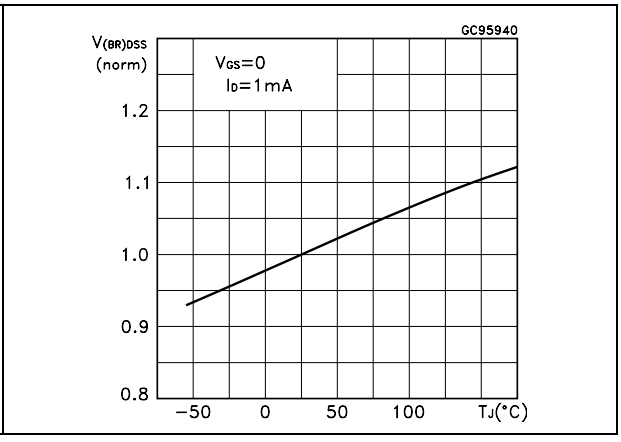


Figure 12. Normalized B_{VDSS} vs temperature



3 Test circuit

Figure 13. Switching times test circuit for resistive load

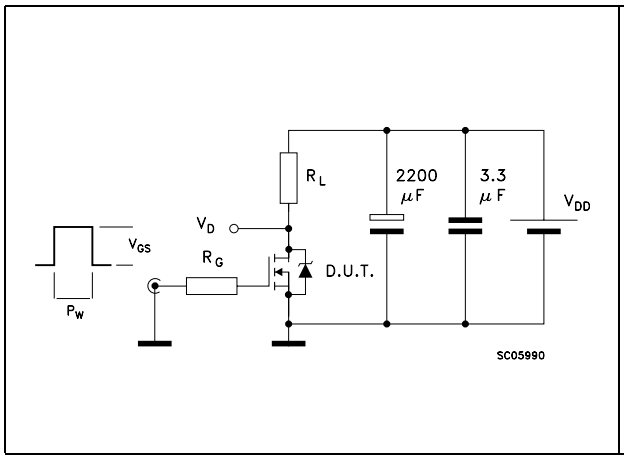


Figure 14. Gate charge test circuit

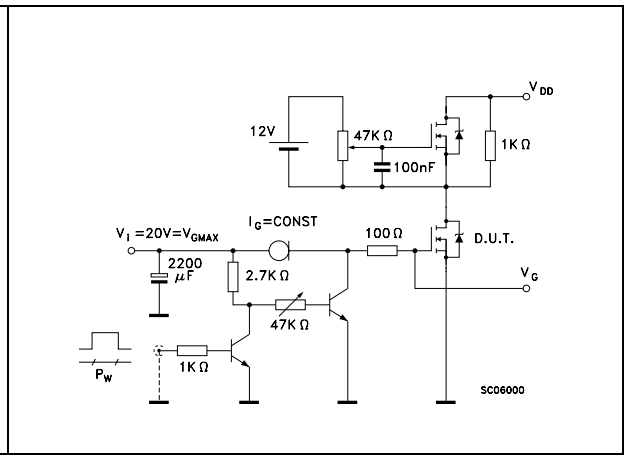


Figure 15. Test circuit for inductive load switching and diode recovery times

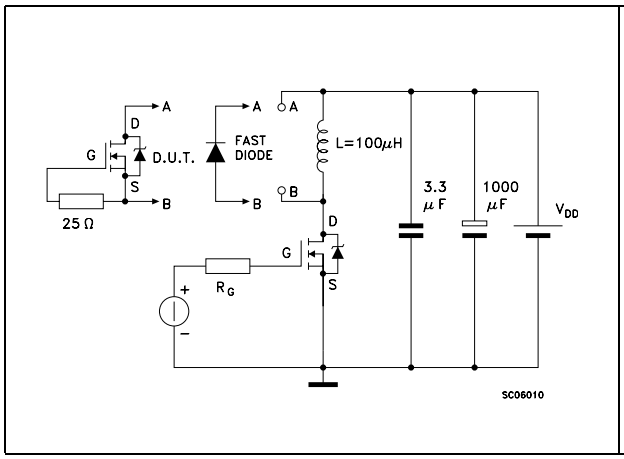


Figure 16. Unclamped Inductive load test circuit

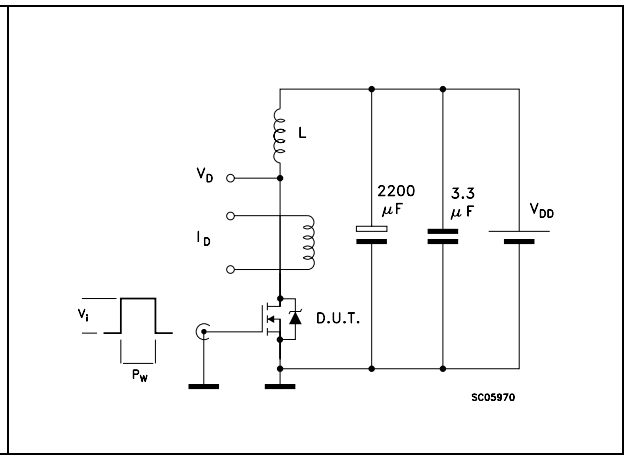


Figure 17. Unclamped inductive waveform

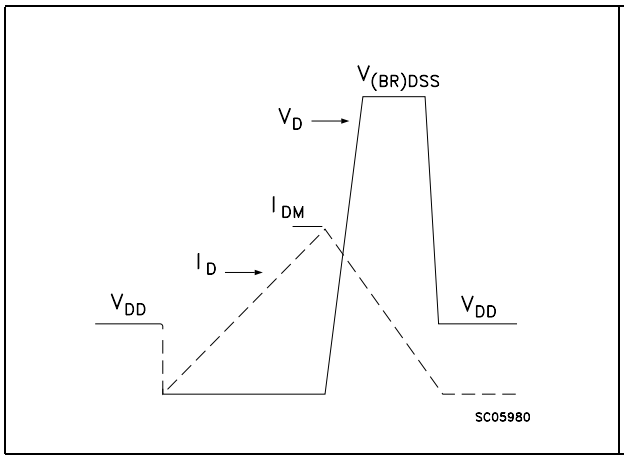
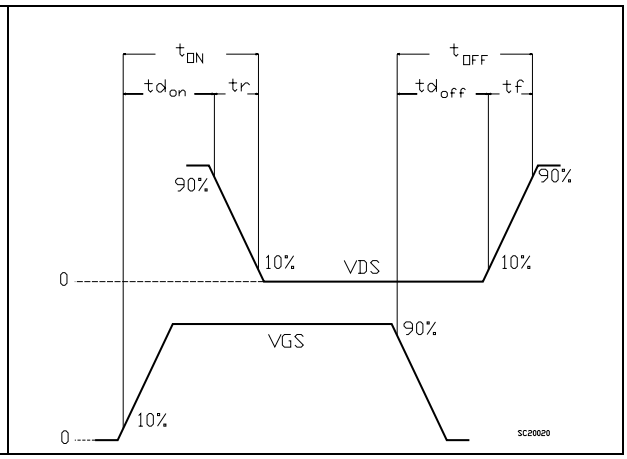


Figure 18. Switching time waveform

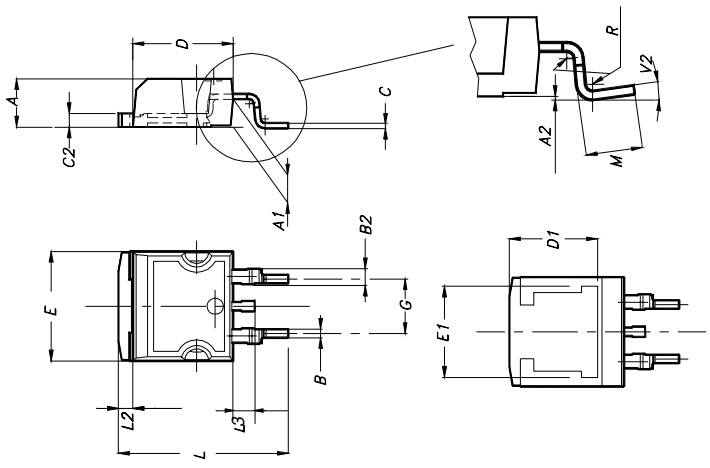


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

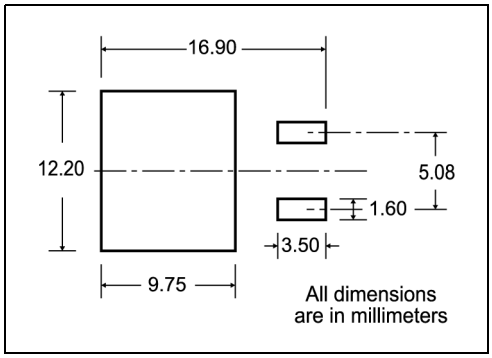
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			

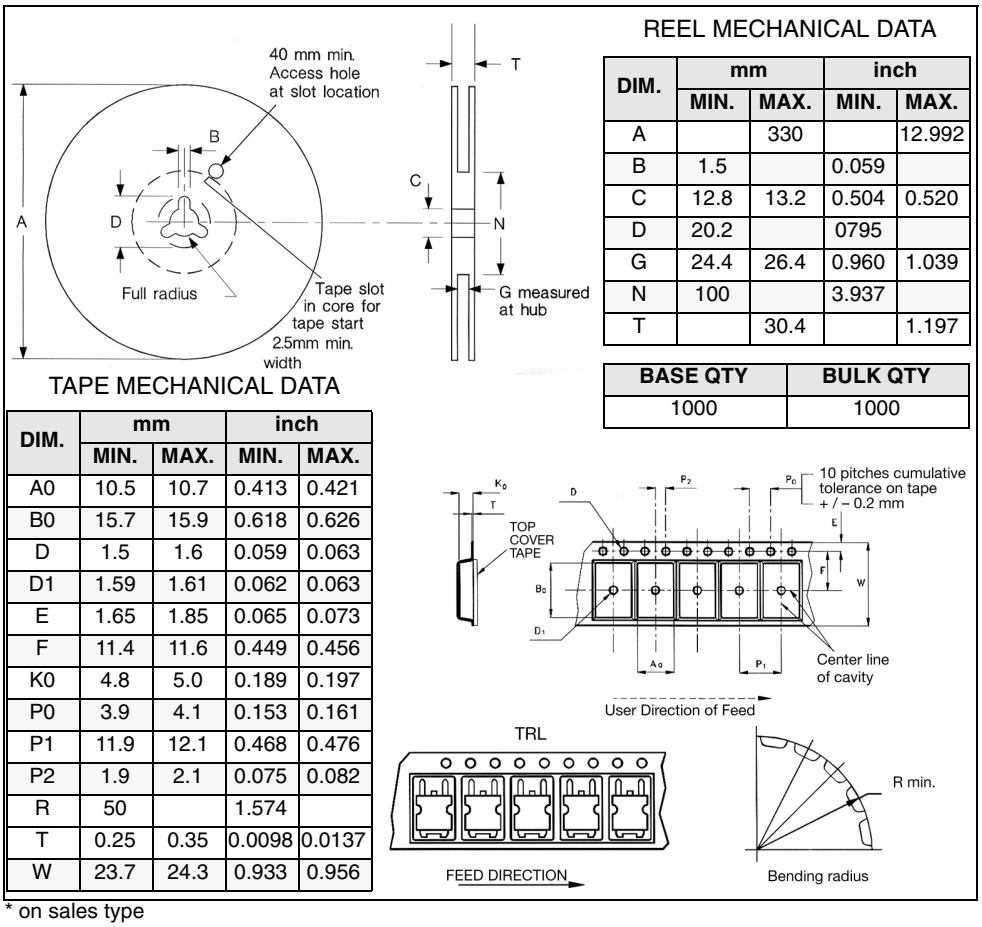


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

* on sales type

6 Revision history

Table 6. Document revision history

Date	Revision	Changes
21-Jun-2006	3	Preliminary document
12-Jun-2006	4	New template

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